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60 V, single N-channel Trench MOSFET

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protected

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage	_		-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	170	mA
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C		-	3	4.5	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 ☐ ☐ 2 SC-70 (SOT323)	G G S S 017aaa255

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
NX7002AKW	SC-70	plastic surface-mounted package; 3 leads	SOT323		

4. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
NX7002AKW	AH%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

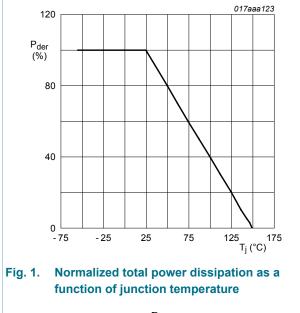
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	100	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	680	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	220	mW
			[1]	-	255	mW

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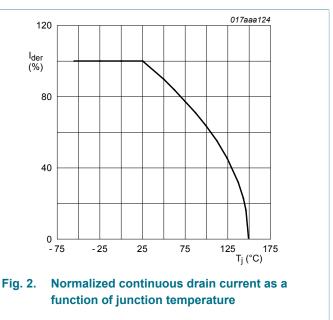
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{sp} = 25 °C		-	1060	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	170	mA

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



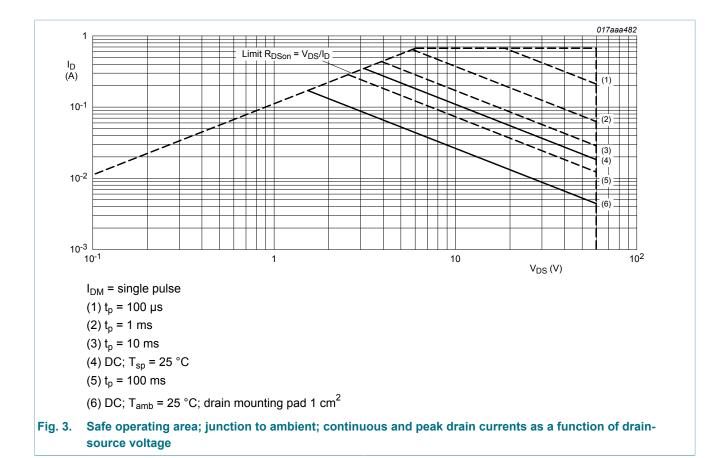
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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6. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance	_	[1]	-	485	560	K/W
	from junction to ambient		[2]	-	420	480	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

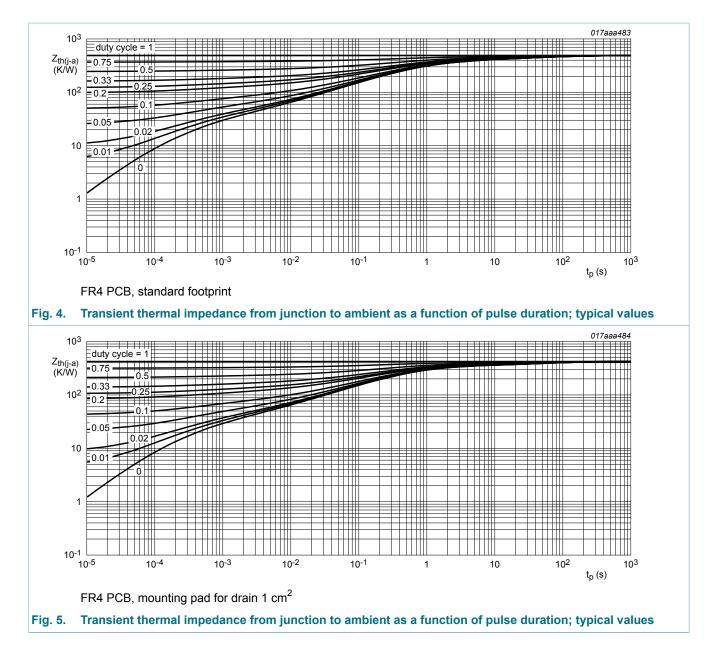
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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7. Characteristics

Table 7. C	haracteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C		-	-	10	μA
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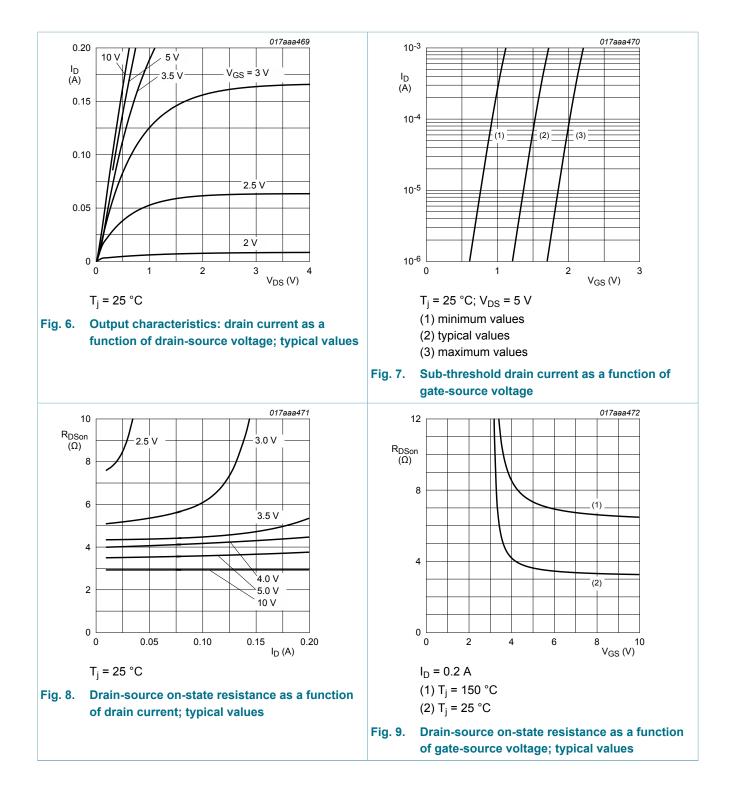
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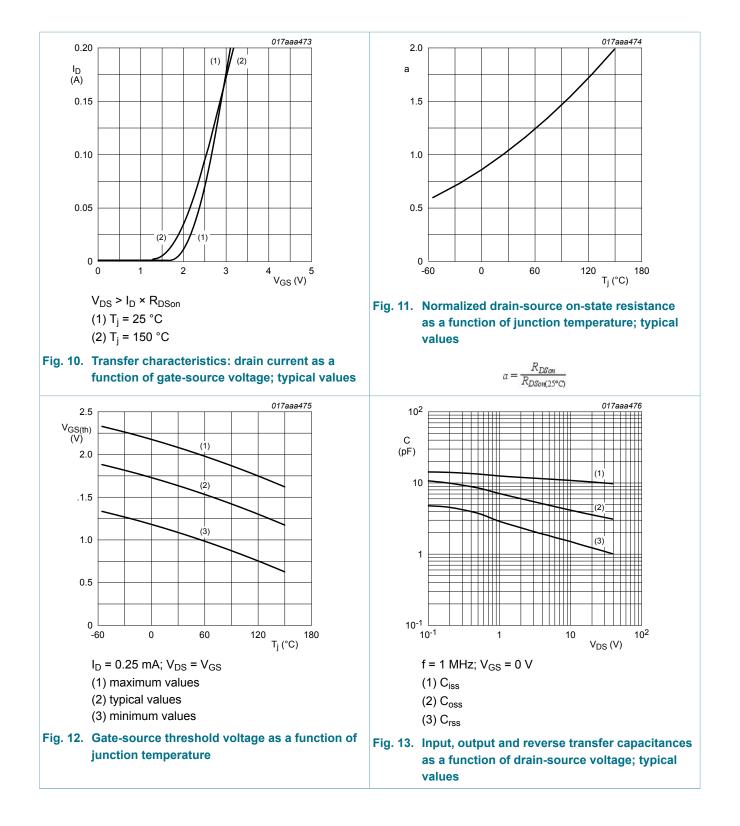
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	2	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	2	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
		V_{GS} = 5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	3	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	6.2	9.2	Ω
		V_{GS} = 5 V; I _D = 100 mA; T _j = 25 °C	-	3.7	5.2	Ω
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	230	-	mS
Dynamic cl	naracteristics	· · · ·				
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I _D = 200 mA; V _{GS} = 4.5 V;	-	0.33	0.43	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q _{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	11	17	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.4	-	pF
C _{rss}	reverse transfer capacitance		-	1.4	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R _L = 250 Ω; V _{GS} = 10 V;	-	6	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t _{d(off)}	turn-off delay time		-	20	40	ns
t _f	fall time		-	14	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _I = 25 °C	0.47	0.7	1.2	V

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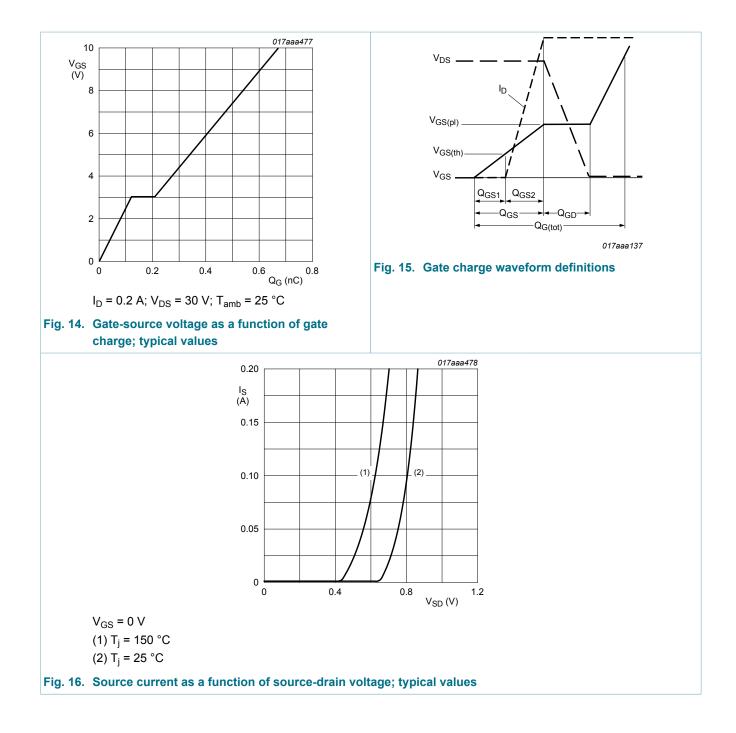


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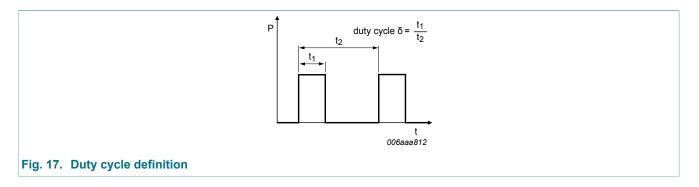
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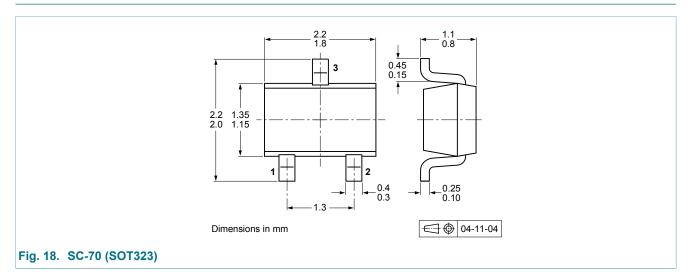


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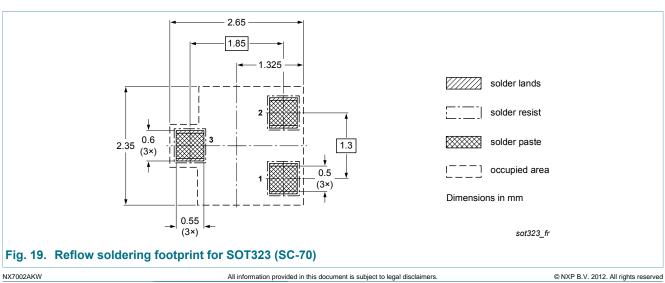
Test information 8.



Package outline 9.

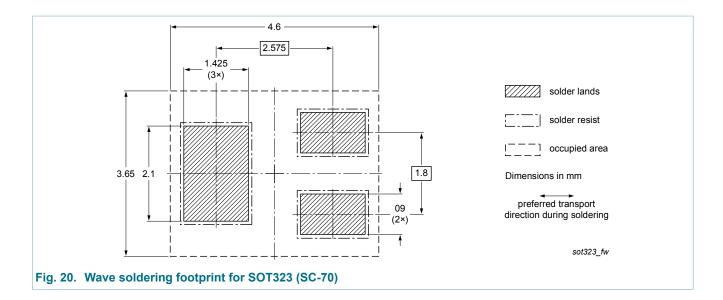


10. Soldering



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11. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002AKW v.2	20120711	Product data sheet	-	NX7002AKW v.1
Modifications:	Characteristics: I _{GSS} value corrected			
NX7002AKW v.1	20120301	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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